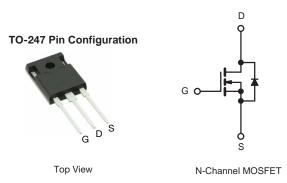


N-Channel 800 V (D-S) Super Junction Power MOSFET

PRODUCT SUMMARY					
V _{DS} (V)@T _j (max)	R _{DS(on)} (mΩ)(Typ.)	I _D (A)	Q _g (Typ.)		
850	62 at V_{GS} = 10 V	40	163 nC		



FEATURES

- DT-SJ Power MOSFET
- 100 % Rg and UIS tested
- Low R_{DS(ON)}×FOM
- Extremely low switching loss
- Excellent stability and uniformity

APPLICATIONS

- PC power
- Telecom power
- Server power
- LED Light
- EV Charger

ABSOLUTE MAXIMUM RATINGS ($T_C = 25 \text{ °C}$, unless otherwise noted)					
PARAMETER	SYMBOL	LIMIT	UNIT		
Drain-Source Voltage	V _{DS}	800	v		
Gate-Source Voltage	V _{GS}	± 30	v		
Continuous Drain Current (T _J = 150 °C) ^a	T _C = 25 °C		40	А	
	T _C = 100 °C	I _D	24.3		
Pulsed Drain Current ^b		I _{DM}	I _{DM} 120		
Single Avalanche Energy ^e		E _{AS}	2300	mJ	
Maximum Power Dissipation ^c	$T_C = 25 \ ^\circ C$	D	415	w	
	T _C = 100 °C		200	vv	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55 to +150	°C	

THERMAL RESISTANCE RATINGS					
PARAMETER	SYMBOL	LIMIT	UNIT		
Junction-to-Ambient (PCB Mount) ^d	R _{thJA}	62	°C/W		
Junction-to-Case (Drain)	R _{thJC}	0.3			

Notes

- a. Calculated continuous current based on maximum allowablejunction temperature.
- b. Repetitive rating; pulse width limited by max. junction temperature.
- c. Pd is based on max. junction temperature, using junction-case thermal resistance.
- d. The value of ReuA is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with Ta=25 °C.
- e. V_{DD}=300 V,V_{GS}=10 V, L=40mH, starting T_j=25 °C.





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SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)						
PARAMETER	SYMBOL TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static						
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS}=0~V,~I_D=250~\mu A$	800	-	-	V
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 2 \text{ mA}$	2	-	4	
Gate-Body Leakage	I _{GSS}	V_{DS} = 0 V, V_{GS} = ± 30 V	-	-	± 100	nA
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = 800 \text{ V}, V_{GS} = 0 \text{ V}$	-	-	10	μA
Drain-Source On-State Resistance a	R _{DS(on)}	$V_{GS} = 10 \text{ V}, \text{ I}_{D} = 20 \text{ A}$	-	62	78	
Brain Oblice on Glate Resistance	TDS(on)	$V_{GS} = 10 \text{ V}, \text{ I}_D = 20 \text{ A}, \text{ T}_j = 150 ^\circ\text{C}$	-	110	-	mΩ
Forward Transconductance ^a	9 _{fs}	$V_{DS} = 50 \text{ V}, I_D = 20 \text{ A}$	-	40	-	S
Dynamic ^b			·		•	
Input Capacitance	Ciss		-	7556	-	pF
Output Capacitance	C _{oss}	$V_{GS} = 0 \text{ V}, V_{DS} = 50 \text{ V}, \text{ f} = 100 \text{ KHz}$	-	410	-	
Reverse Transfer Capacitance	C _{rss}		-	6.8	-	
Total Gate Charge ^c	Qg		-	163	-	
Gate-Source Charge ^c	Q _{gs}	V_{DS} = 400 V, V_{GS} = 10 V, I_{D} = 40 A	-	28	-	nC
Gate-Drain Charge ^c	Q _{gd}		-	55	-	
Gate Resistance	Rg	f = 1 MHz	-	2.8	-	Ω
Turn-On Delay Time ^c	t _{d(on)}		-	44	-	
Rise Time ^c	t _r	$V_{DD} = 400 \text{ V}, \text{ I}_{D} = 10 \text{ A},$	-	88	-	
Turn-Off Delay Time ^c	t _{d(off)}	$V_{GEN}=10~V,~R_{g}=2~\Omega$	-	105	-	ns .
Fall Time ^c	t _f		-	9	-	
Drain-Source Body Diode Ratings and	nd Characteris	stics ^b (T _C = 25 °C)			•	
Continuous Source Current	۱ _S	T _C = 25 °C	-	-	40	А
Pulsed Current (t = 100 µs)	I _{SM}		-	-	120	А
Forward Voltage ^a	V _{SD}	I_{S} =40 A, V_{GS} = 0 V	-	-	1.3	V
Reverse Recovery Time	t _{rr}		-	440	-	ns
Reverse Recovery Charge	Q _{rr}	$I_S = 20$ A, di/dt = 100 A/ μ s	-	9.3	-	μC
Peak reverse recovery current	I _{rrm}		-	40.5	-	А

Notes

a. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%.$

b. Guaranteed by design, not subject to production testing.

c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

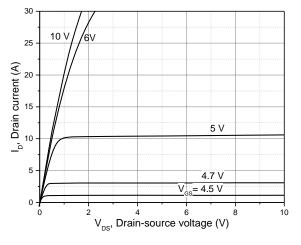


Figure 1. Typ. output characteristics

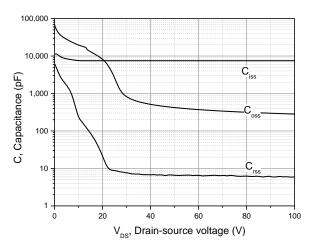


Figure 3. Typ. capacitances

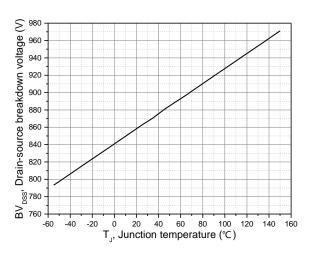


Figure 5. Drain-source breakdown voltage

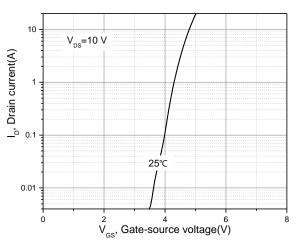


Figure 2. Typ. transfer characteristics

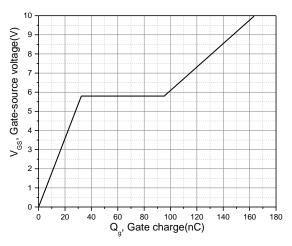


Figure 4. Typ. gate charge

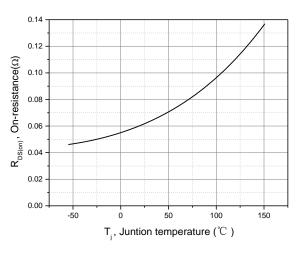
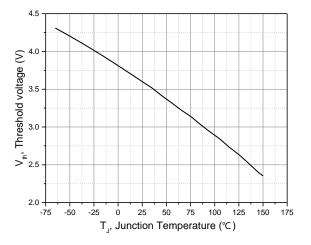


Figure 6. Drain-source on-state resistance



TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)





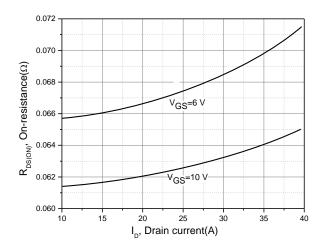


Figure 9. Drain-source on-state resistance

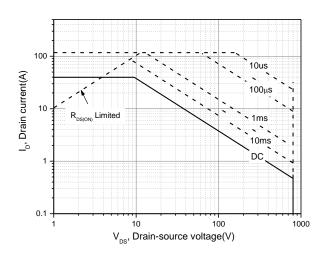


Figure 11. Safe operation area T_C=25 °C

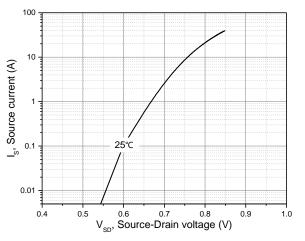


Figure 8. Forward characteristic of body diode

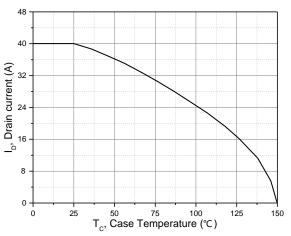
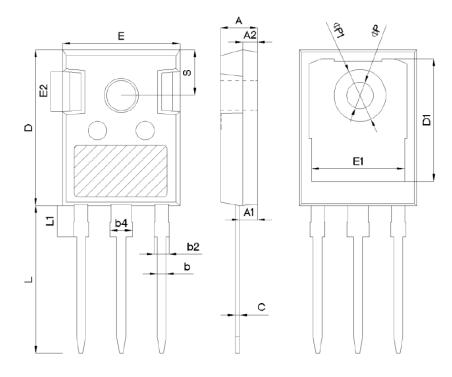


Figure 10. Drain current



TO-247-C PACKAGE OUTLINE



		mm		
Symbol	Min	Nom	Max	
A	4.80	5.00	5.20	
A1	2.21	2.41	2.61	
A2	1.85	2.00	2.15	
b	1.11	1.21	1.36	
b2	1.91	2.01	2.21	
b4	2.91	3.01	3.21	
С	0.51	0.61	0.75	
D	20.70	21.00	21.30	
D1	16.25	16.55	16.85	
E	15.50	15.80	16.10	
E1	13.00	13.30	13.60	
E2	4.80	5.00	5.20	
E3	2.30	2.50	2.70	
E	5.44BSC			
L	19.62	19.92	20.22	
L1	-	-	4.30	
ΦP	3.40	3.60	3.80	
ΦP1	-	-	7.30	
S		6.15BSC		



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